

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

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Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China











20V P-Channel MOSFET with Schottky Diode

TDFN 2x2

Pin Definition:

1. Anode	6. Cathode
2. NC	5. Gate
3. Drain	Source

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)
	94 @ V _{GS} = -4.5V	-2.8
-20	131 @ V _{GS} = -2.5V	-2.3
	185 @ V _{GS} = -1.8V	-0.54

SCHOTTKY PRODUCT SUMMARY

V _R (V)	V _F (V)	I _F (A)
20	0.5	2

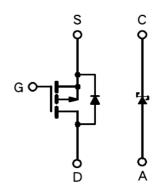
Features

- Configuration with MOSFET and Low Vf SKY
- Package low profile 0.75mm (Typ)
- Independent Pin Out for Design Flexibility

Application

- Load Switch for Portable Applications
- DC-DC Buck Circuit
- Li-ion Battery Applications
- Cellular Charger Switch

Block Diagram



P-Channel MOSFET with Schottky Diode

Ordering Information

Part No.	Package	Packing
TSM301K12CQ RFG	TDFN 2x2	3Kpcs / 7" Reel

Note: "G" denotes for Halogen Free

MOSFET Absolute Maximum Rating (T_A=25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	-20	V
Gate-Source Voltage		V_{GS}	±12	V
Continuous Drain Current (Note 1,2)		I _D	-4.5	Α
Pulsed Drain Current		I _{DM}	-8	Α
Marian and Danier Distriction	T _C =25 °C	I _D	6.5	W
Maximum Power Dissipation	T _A =25 °C (Note 2)		1.56	W
Operating Junction Temperature		T_J	+150	°C
Operating Junction and Storage Temperature Range		T_J, T_{STG}	- 55 to +150	°C

Schottky Absolute Maximum Rating (T_A=25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit
Reverse Voltage		V_{R}	20	V
Average Forward Current (Note 1,2)		I _F	2	Α
Pulsed Forward Current		I _{FM}	5	Α
Manigarya Davian Dissination (Nets 4)	T _C =25 °C	P_D	6.8	W
Maximum Power Dissipation (Note 1)	T _A =25 °C (Note 2)		1.47	W



Pb RoHS

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Thermal Resistance Ratings

Parameter		Symbol	Limit	Unit	
MOSFET					
Thermal Desistance Investigate Ambient	T≤ 5s	DO	80	°C/W	
Thermal Resistance-Junction to Ambient	Steady State	$R\Theta_{JA}$	120	°C/W	
Schottky					
Thermal Desistance Investigate Ambient	T ≤ 5s	DO.	85	°C/W	
Thermal Resistance-Junction to Ambient	Steady State	$R\Theta_{JA}$	130	°C/W	

Notes

- 1. Surface mounted on 1" x 1" (2 oz) FAR4 board,
- 2. t ≤ 5s

MOSFET Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250uA$	BV _{DSS}	-20		1	V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	$V_{GS(TH)}$	-0.5			V
Gate Body Leakage	$V_{GS} = \pm 12V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = -20V, V_{GS} = 0V$	I _{DSS}	1		-1	μΑ
	$V_{GS} = -4.5V, I_{D} = -2.8A$				94	
Drain-Source On-State Resistance ^a	$V_{GS} = -2.5V, I_{D} = -2.3A$	R _{DS(ON)}	1		131	mΩ
	$V_{GS} = -1.8V, I_{D} = -0.54A$	===(=::,	1		185	
Diode Forward Voltage	$I_S = -1.6A, V_{GS} = 0V$	V_{SD}			-1.2	V
Dynamic ^b						
Total Gate Charge	V CV I 0.0A	Q_g		5.2	10	
Gate-Source Charge	$V_{DS} = -6V, I_{D} = -2.8A,$	Q_gs		1.36		nC
Gate-Drain Charge	$V_{GS} = -5V$	Q_{gd}		0.6		
Input Capacitance	VOO 0V VD0 0V	C _{iss}		5.2		
Output Capacitance	VGS=0V, VDS=-6V,	C _{oss}		9.7		pF
Reverse Transfer Capacitance	f =1.0MHz	C _{rss}		19		
Switching ^c						
Turn-On Delay Time		t _{d(on)}		29		
Turn-On Rise Time	VDS=-15V, RD=15Ω,	t _r		295		0
Turn-Off Delay Time	RG=6Ω, VGS=-10V	t _{d(off)}		170		nS
Turn-Off Fall Time		t _f		65		

Schottky Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Forward Voltage Drop	I _F = 1A	V _F	1		0.5	V
Maximum Reverse Leakage	$V_R = 5V$		1	0.015	0.08	Л
Current	V _R = 20V	I _{Rm}	1	0.02	0.10	mA
Junction Capacitance	V _R = 10V	Ст		60		pF

Notes:

- a. pulse test: PW ≤300µS, duty cycle ≤2%
- b. For DESIGN AID ONLY, not subject to production testing.
- c. Switching time is essentially independent of operating temperature.

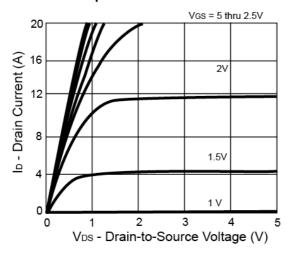




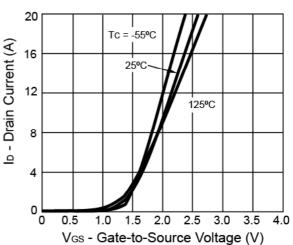
20V P-Channel MOSFET with Schottky Diode

MOSFET Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

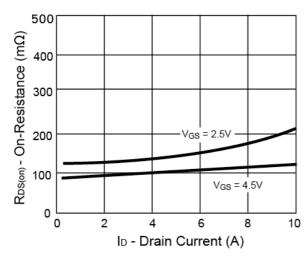
Output Characteristics



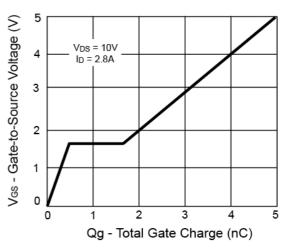
Transfer Characteristics



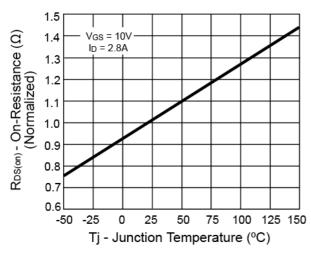
On-Resistance vs. Drain Current



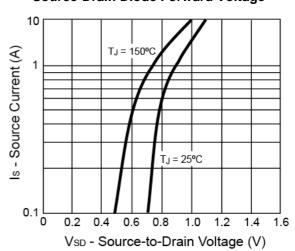
Gate Charge



On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



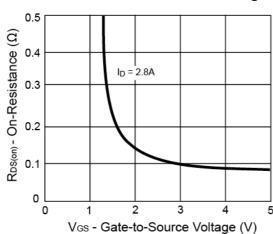




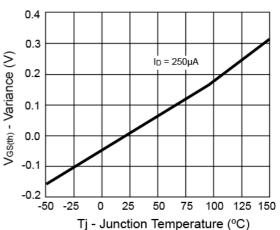


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

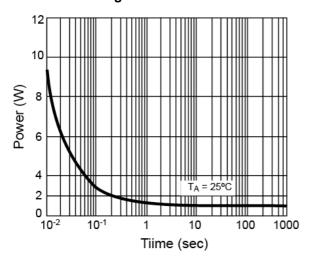
On-Resistance vs. Gate-Source Voltage



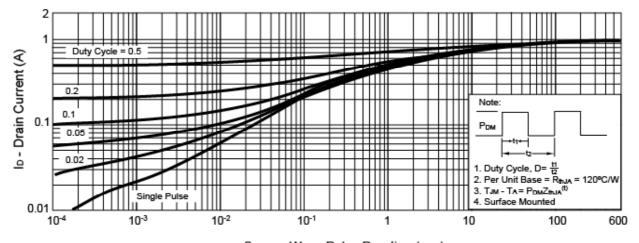
Threshold Voltage



Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient



Square Wave Pulse Duration (sec)

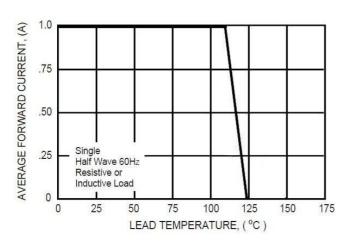




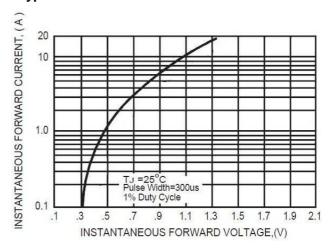


SCHOTTKY Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

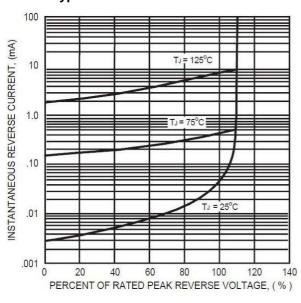
Typical Forward Current Derating Curve



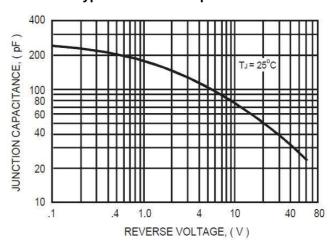
Typical Instantaneous Forward Characteristics



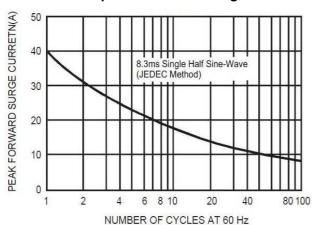
Typical Reverse Characteristics



Typical Junction Capacitance



Maximum Repetitive Forward Surge Current

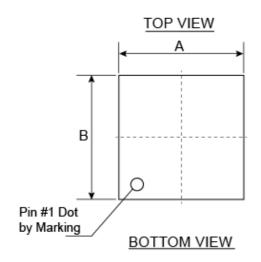




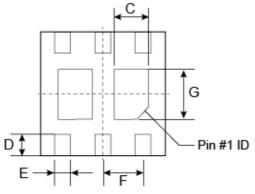


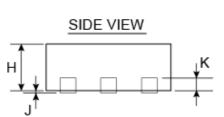
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TDFN 2x2 Mechanical Drawing

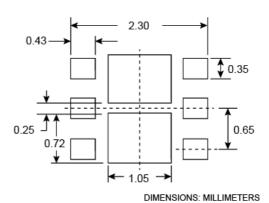


DIM MILLIME		ETERS	INC	HES
ואווט	MIN	MAX	MIN	MAX
Α	1.95	2.05	0.0768	0.0807
В	1.95	2.05	0.0768	0.0807
С	0.50	0.60	0.0197	0.0236
D	0.30	0.40	0.0118	0.0157
E	0.20	0.30	0.0079	0.0118
F	0.65	BSC	0.025	6 BSC
G	0.75	0.85	0.0295	0.0335
Н	0.70	0.80	0.0276	0.0315
J	-	0.05	-	0.0020
K	0.195	0.211	0.0077	0.0083





SOLDERING FOOTPRINT



Marking Diagram

3K12 YML Y = Year Code

M = Month Code for Halogen Free Product (O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)

L = Lot Code



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